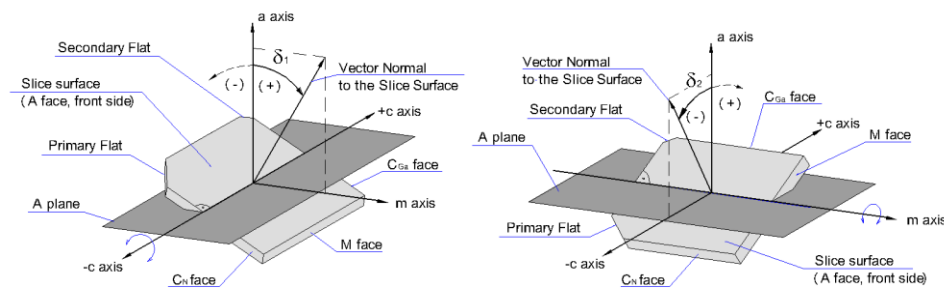


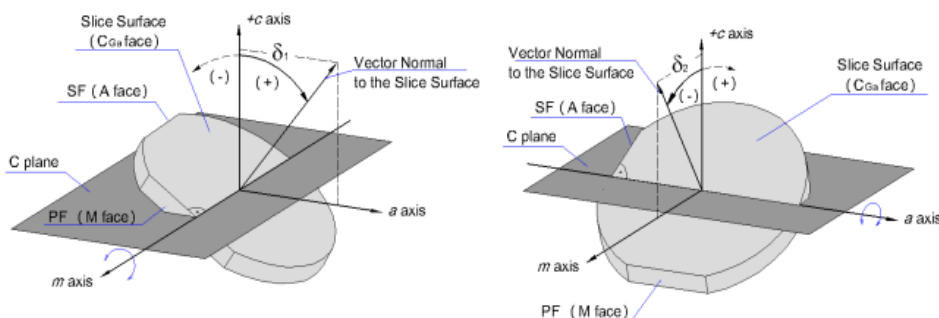
The substrate is sliced from a mono-crystalline bulk material grown by ammonothermal method.

TECHNICAL SPECIFICATION		
Features	Units	Available planes
		C-plane (0001)
Carrier concentration	cm <sup>-3</sup>	2x10 <sup>17</sup> -2x10 <sup>18</sup>
Dopant		Oxygen-doped
Resistivity	Ωcm	10 <sup>-2</sup> -10 <sup>-1</sup>
Mobility	cm <sup>2</sup> /Vs	~ 200-250
Thickness	μm	300-400
Total thickness variation (TTV)	μm	≤40
Bow	μm	≤10
FWHM (0002) of X-ray rocking curve, epi-ready surface at 100 μm x 100 μm slit	arcsec	~20
Dislocation density (EPD)	cm <sup>-2</sup>	< 5 x 10 <sup>4</sup>
Misorientation	deg	Od demand
Surface finishing	Front side	Mechano-chemically polished (epi-ready RMS < 5 nm)
	Back side	Lapped
Available sizes		10x10
		1-inch
		2-inch
Available grades		Test grade Production grade Prime grade
Packaging		Separate single wafer container
Special request		For pricing or technical enquiries please contact our sales team

### Square shape



### Round shape



**Note:**

The information given above may be subject to change at any time without notice. This leaflet is not an offer within the meaning of sales or commercial law. The AMMONO-GaN substrates are offered for sale under Ammono's General Terms and Conditions.